

## Product Summary

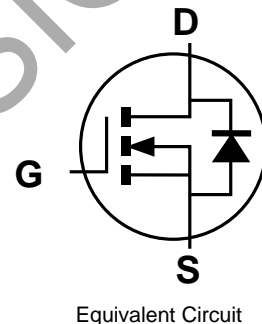
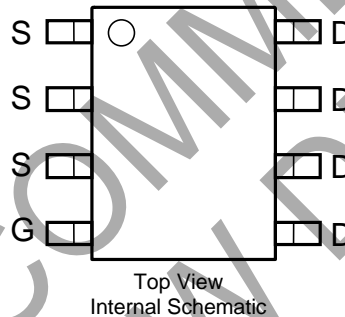
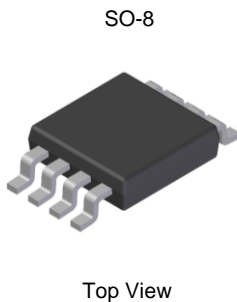
$V_{(BR)DSS}$	$R_{DS(ON)}$ max	$I_D$ max $T_A = +25^\circ\text{C}$
30V	11m $\Omega$ @ $V_{GS} = 10\text{V}$	10.3A
	15m $\Omega$ @ $V_{GS} = 4.5\text{V}$	9.3A

## Description

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- Backlighting
- Power Management Functions
- DC-DC Converters



## Features and Benefits

- 100% Unclamped Inductive Switch (UIS) test in production
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

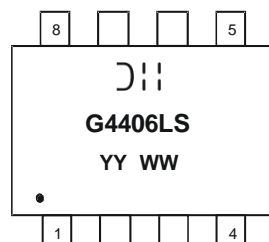
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMG4406LSS-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



⑆ = Manufacturer's Marking  
 G4406LS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY or YY = Year (ex: 13 = 2013)  
 WW = Week (01 - 53)

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage			$V_{GSS}$	$\pm 20$	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	10.3 8.3	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	13.4 10.6	A
Continuous Drain Current (Note 6) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	9.3 7.3	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	12.0 9.5	A
Maximum Continuous Body Diode Forward Current (Note 6)			$I_S$	2.5	A
Pulsed Drain Current (10 $\mu\text{s}$ pulse, duty cycle = 1%)			$I_{DM}$	90	A
Avalanche Current (Note 7) $L = 0.1\text{mH}$			$I_{AS}$	22	A
Avalanche Energy (Note 7) $L = 0.1\text{mH}$			$E_{AS}$	24	mJ

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Units
Total Power Dissipation (Note 5)			$P_D$	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		$R_{\theta JA}$	80	$^\circ\text{C/W}$
	$t < 10\text{s}$			48	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)			$P_D$	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		$R_{\theta JA}$	61	$^\circ\text{C/W}$
	$t < 10\text{s}$			37	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case			$R_{\theta JC}$	6.4	$^\circ\text{C/W}$
Operating and Storage Temperature Range			$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	30	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	1.35	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	8	11	m $\Omega$	$V_{GS} = 10\text{V}, I_D = 12\text{A}$
		—	12	15		$V_{GS} = 4.5\text{V}, I_D = 10\text{A}$
Forward Transfer Admittance	$ Y_{fs} $	—	32	-	S	$V_{DS} = 5\text{V}, I_D = 12\text{A}$
Diode Forward Voltage	$V_{SD}$	—	0.70	1.0	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	$C_{iss}$	—	1281	—	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	145	—		
Reverse Transfer Capacitance	$C_{rss}$	—	125	—		
Gate resistance	$R_g$	—	1.2	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ( $V_{GS} = 4.5\text{V}$ )	$Q_g$	—	12.5	—	nC	$V_{DS} = 15\text{V}, I_D = 12\text{A}$
Total Gate Charge ( $V_{GS} = 10\text{V}$ )	$Q_g$	—	26.7	—		
Gate-Source Charge	$Q_{gs}$	—	3.6	—		
Gate-Drain Charge	$Q_{gd}$	—	4.4	—		
Turn-On Delay Time	$t_{D(on)}$	—	5.2	—	ns	$V_{DD} = 15\text{V}, V_{GS} = 10\text{V}, R_L = 1.25\Omega, R_G = 3\Omega,$
Turn-On Rise Time	$t_r$	—	21.2	—		
Turn-Off Delay Time	$t_{D(off)}$	—	22.3	—		
Turn-Off Fall Time	$t_f$	—	5.1	—		
Reverse Recovery Time	$t_{rr}$	—	8.5	—	ns	$IF = 12\text{A}, di/dt = 500\text{A}/\mu\text{s}$
Reverse Recovery Charge	$Q_{rr}$	—	7.0	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_J = +25^\circ\text{C}$
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

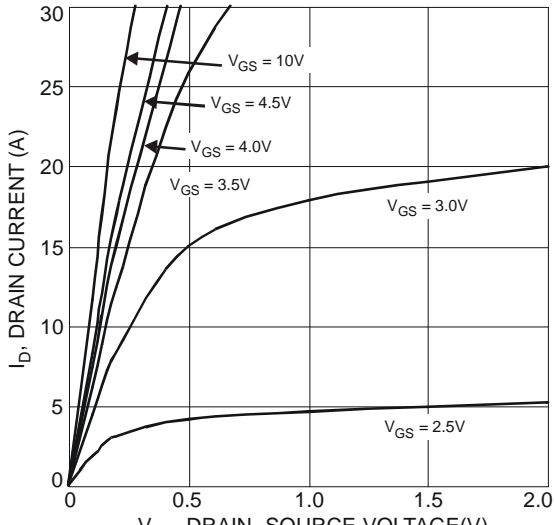


Fig. 1 Typical Output Characteristics

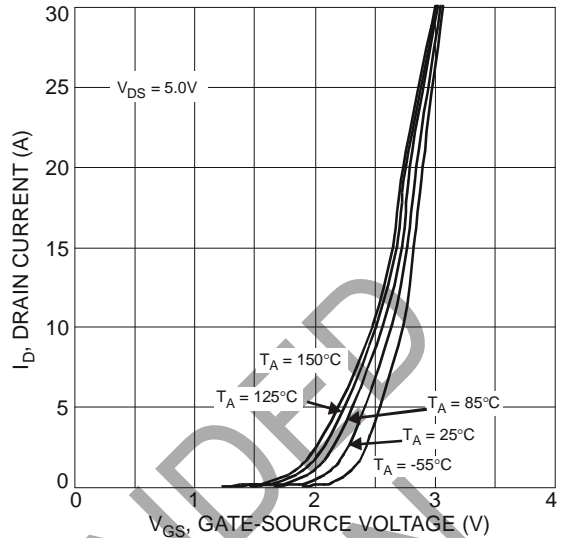


Fig. 2 Typical Transfer Characteristics

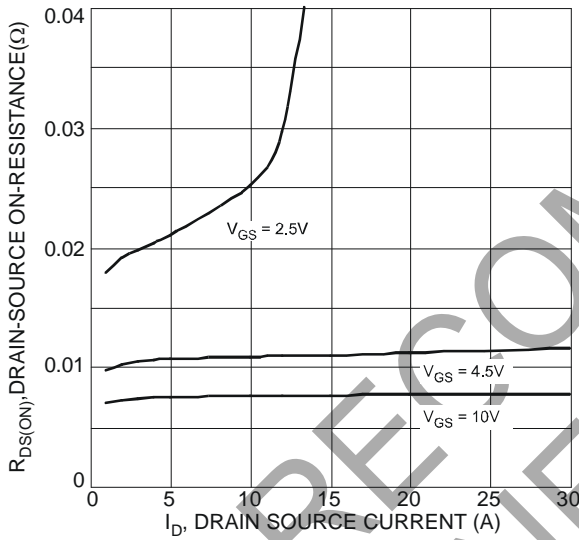


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

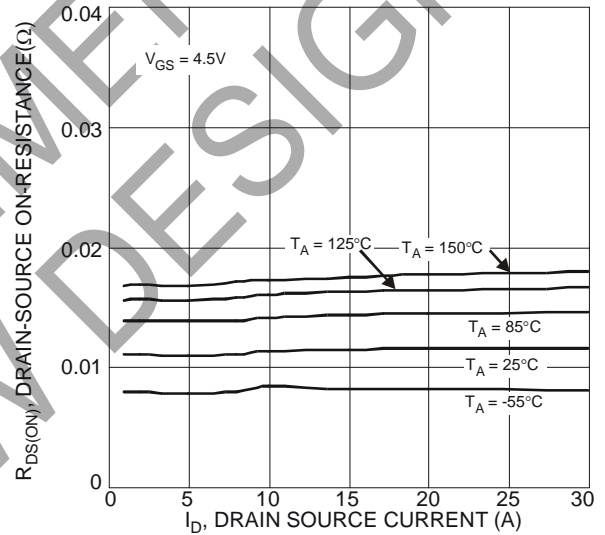


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

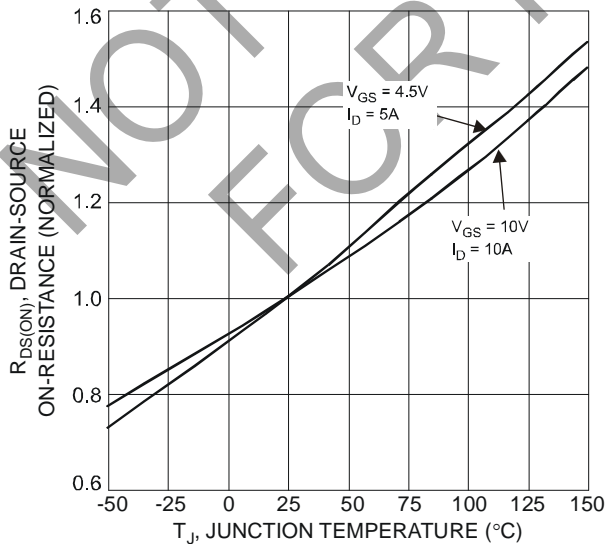


Fig. 5 On-Resistance Variation with Temperature

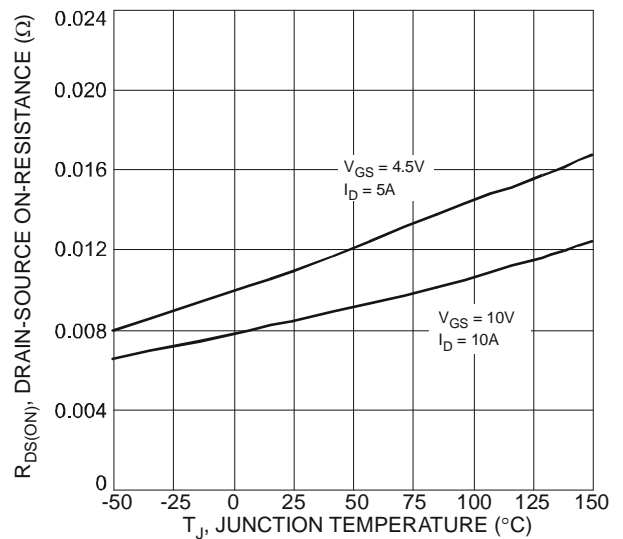


Fig. 6 On-Resistance Variation with Temperature

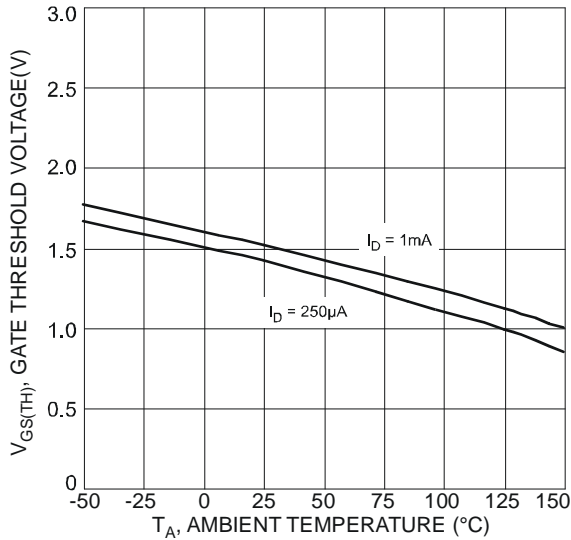


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

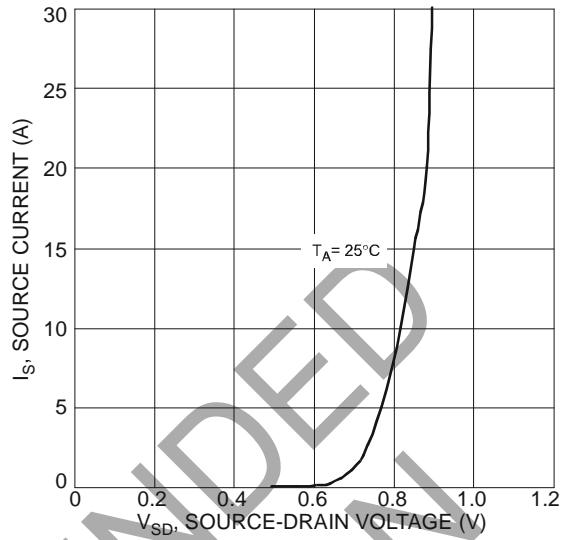


Fig. 8 Diode Forward Voltage vs. Current

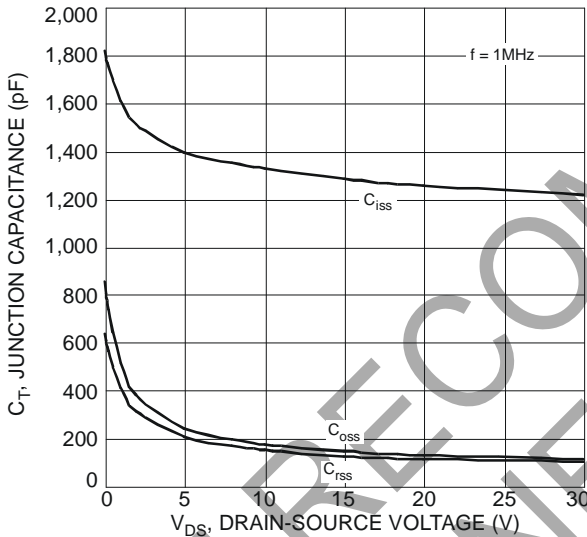


Fig. 9 Typical Junction Capacitance

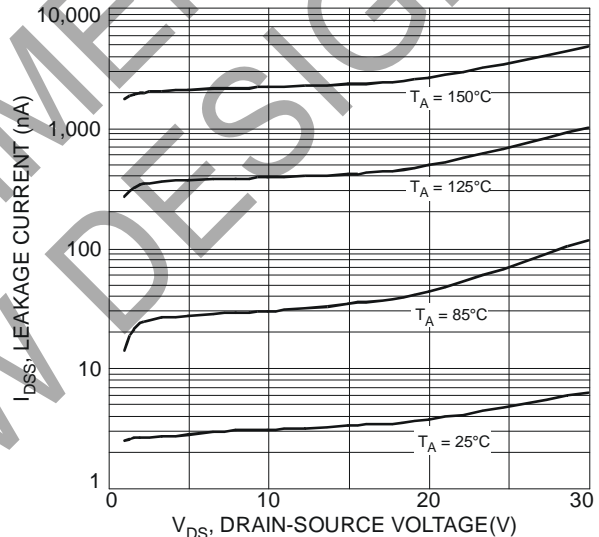


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

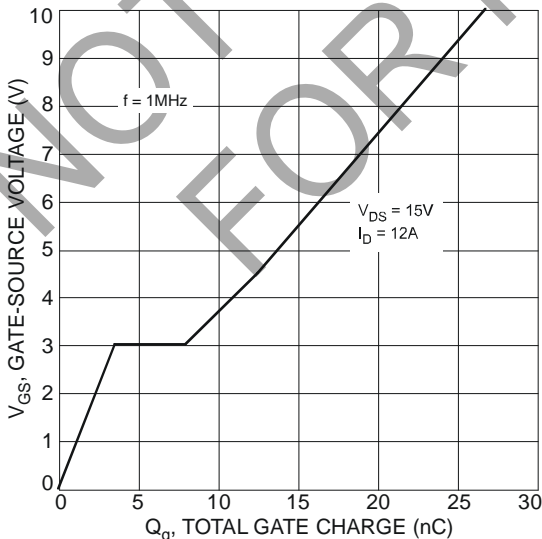


Fig. 11 Gate-Charge Characteristics

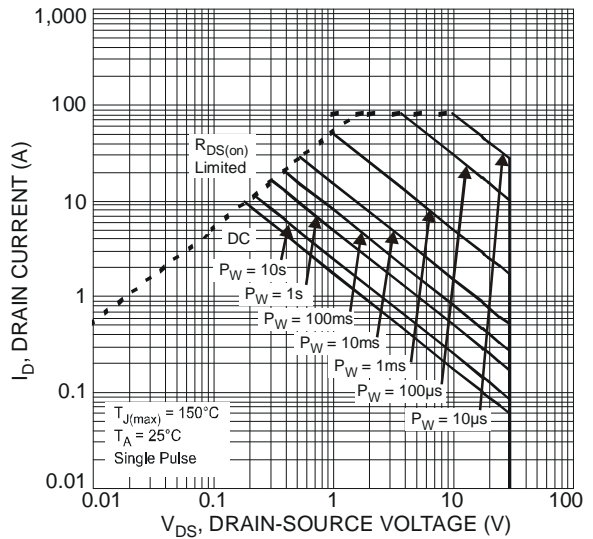
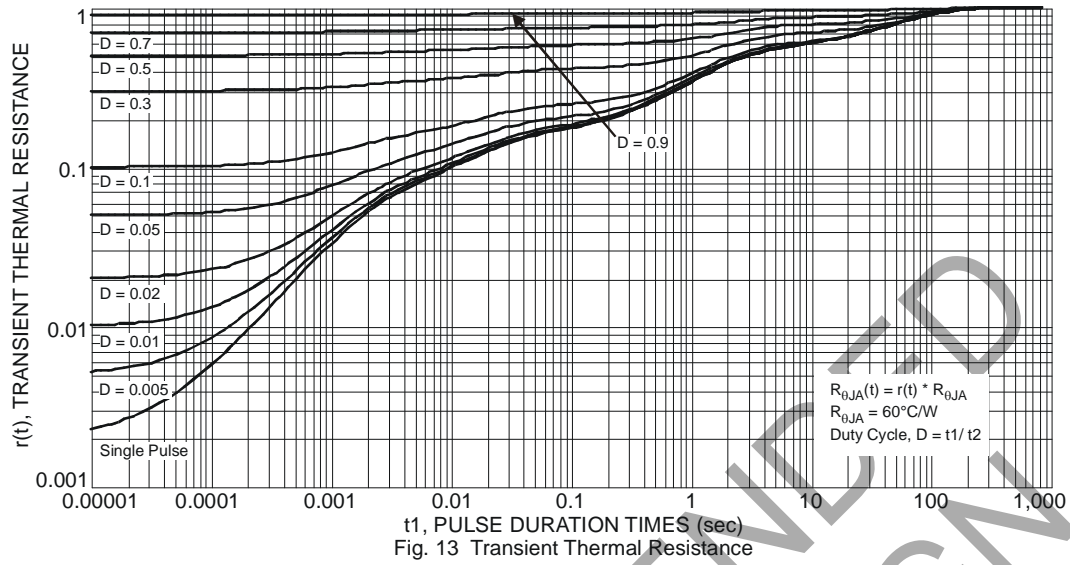
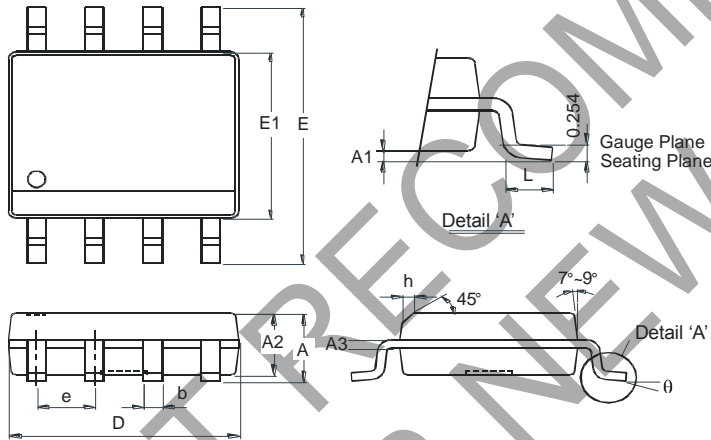


Fig. 12 SOA, Safe Operation Area



**Package Outline Dimensions**

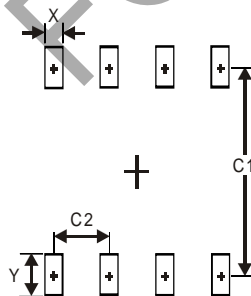
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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